

2SB1606

Silicon PNP epitaxial planar type

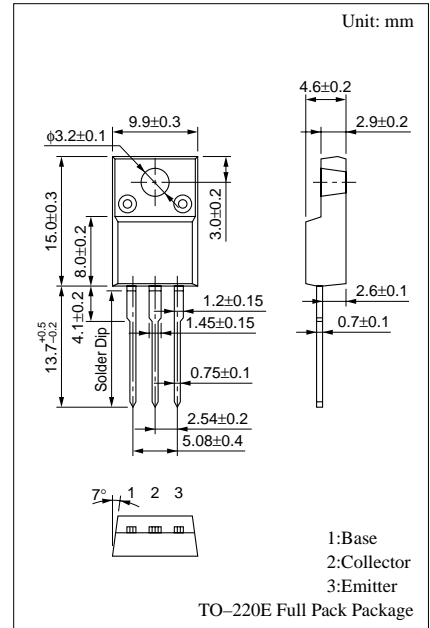
For power switching

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- Full-pack package with outstanding insulation, which can be installed to the heat sink with one screw

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	-130	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-10	A
Collector current	I_C	-5	A
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	40
		$T_a=25^\circ\text{C}$	2
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -100\text{V}, I_E = 0$			-10	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-50	μA
Collector to emitter voltage	V_{CEO}	$I_C = -10\text{mA}, I_B = 0$	-80			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$	45			
	h_{FE2}^*	$V_{CE} = -2\text{V}, I_C = -2\text{A}$	90		260	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4\text{A}, I_B = -0.2\text{A}$			-0.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -4\text{A}, I_B = -0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 10\text{MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -2\text{A}, I_{B1} = -0.2\text{A}, I_{B2} = 0.2\text{A}$		0.13		μs
Storage time	t_{stg}			0.5		μs
Fall time	t_f			0.13		μs

* h_{FE2} Rank classification

Rank	Q	P
h_{FE2}	90 to 180	130 to 260

